

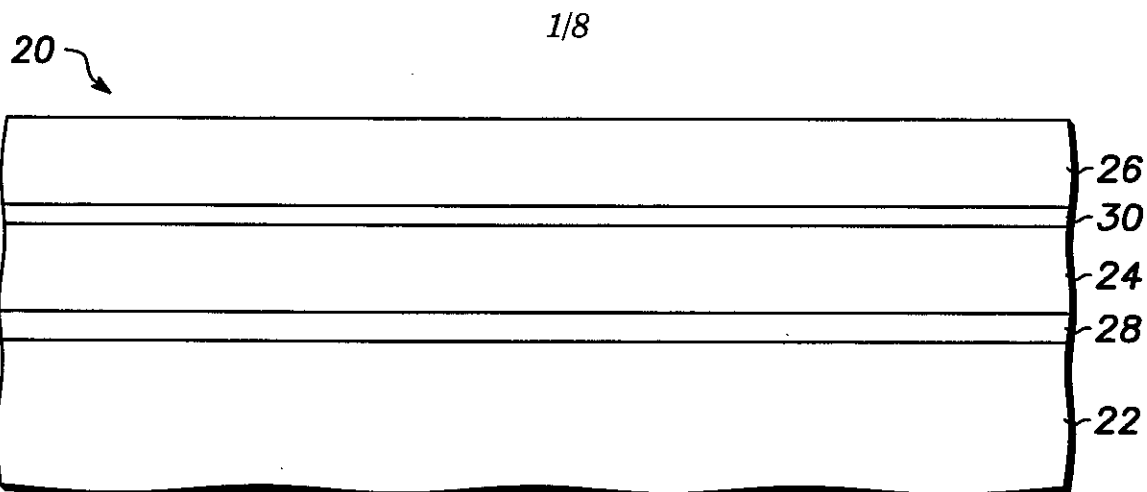


FIG. 1

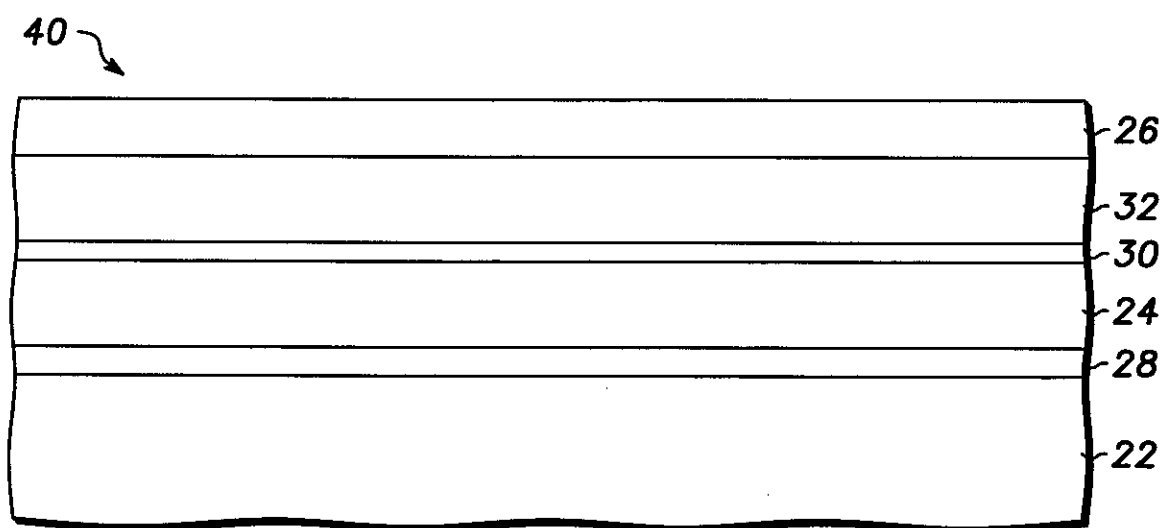


FIG. 2

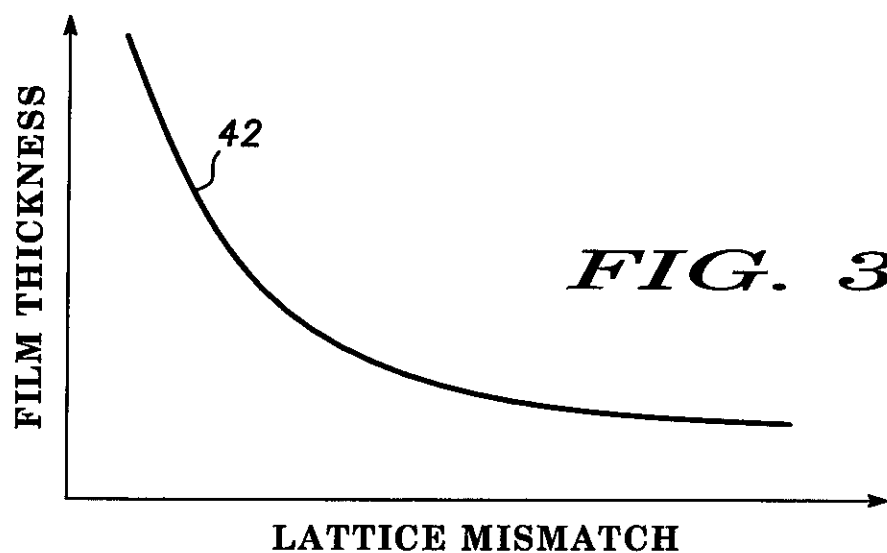


FIG. 3

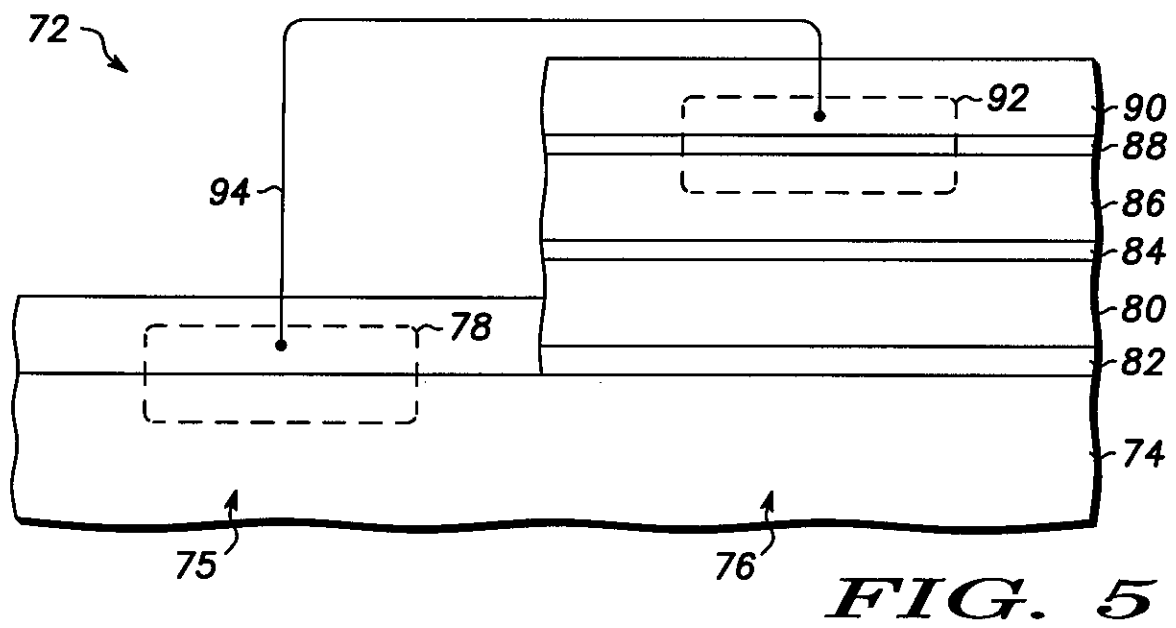
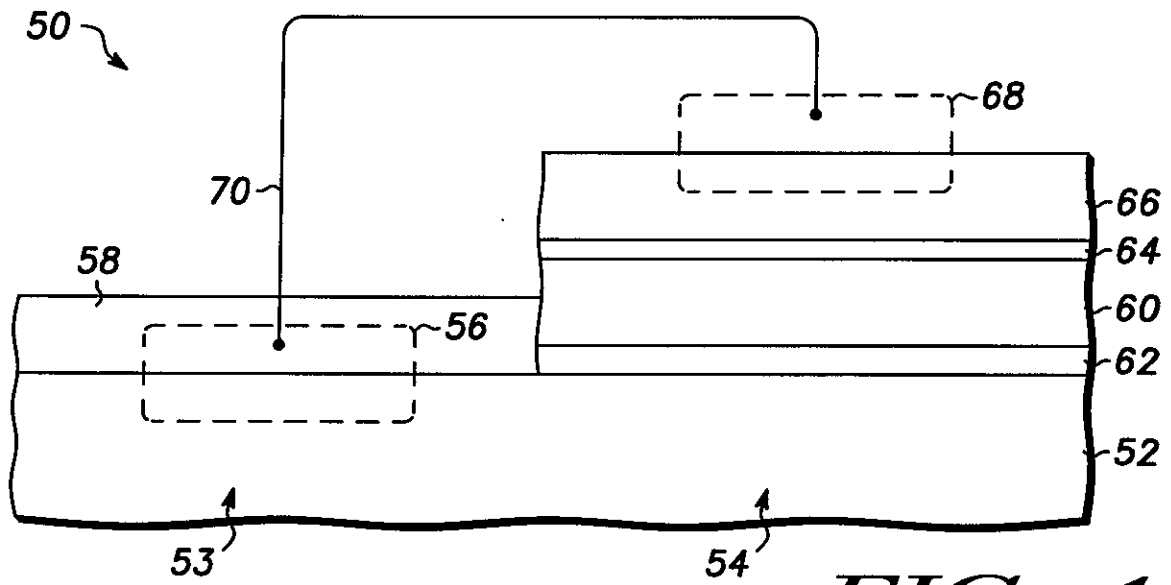
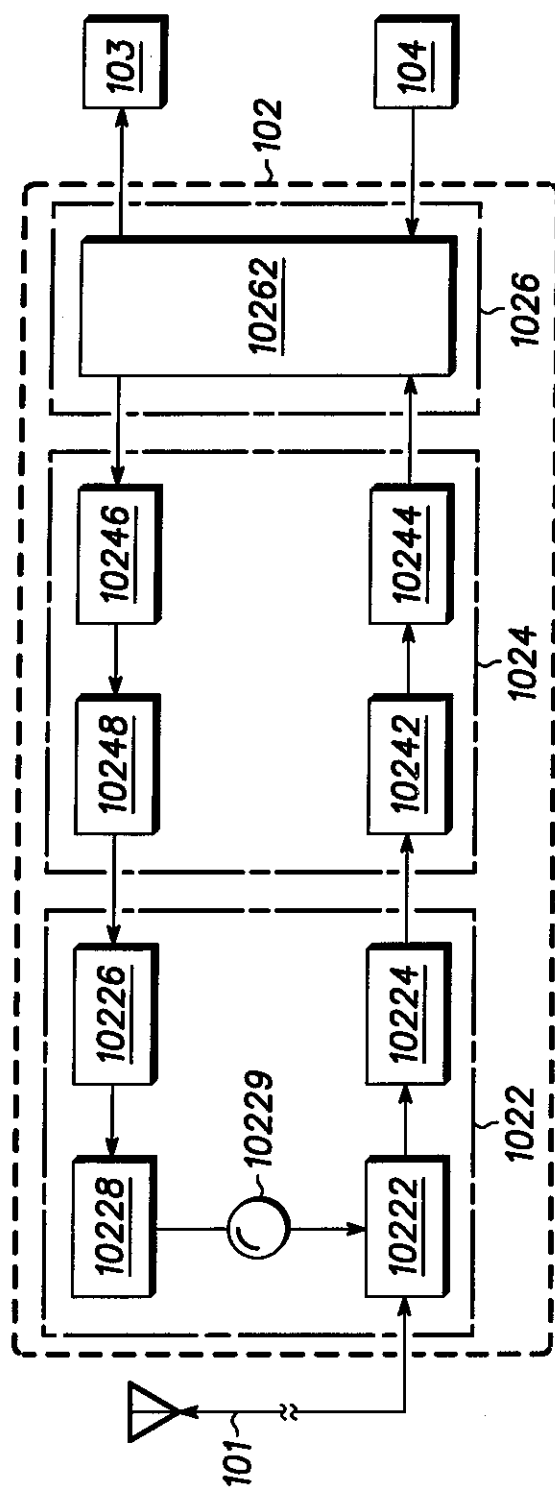


FIG. 6
100

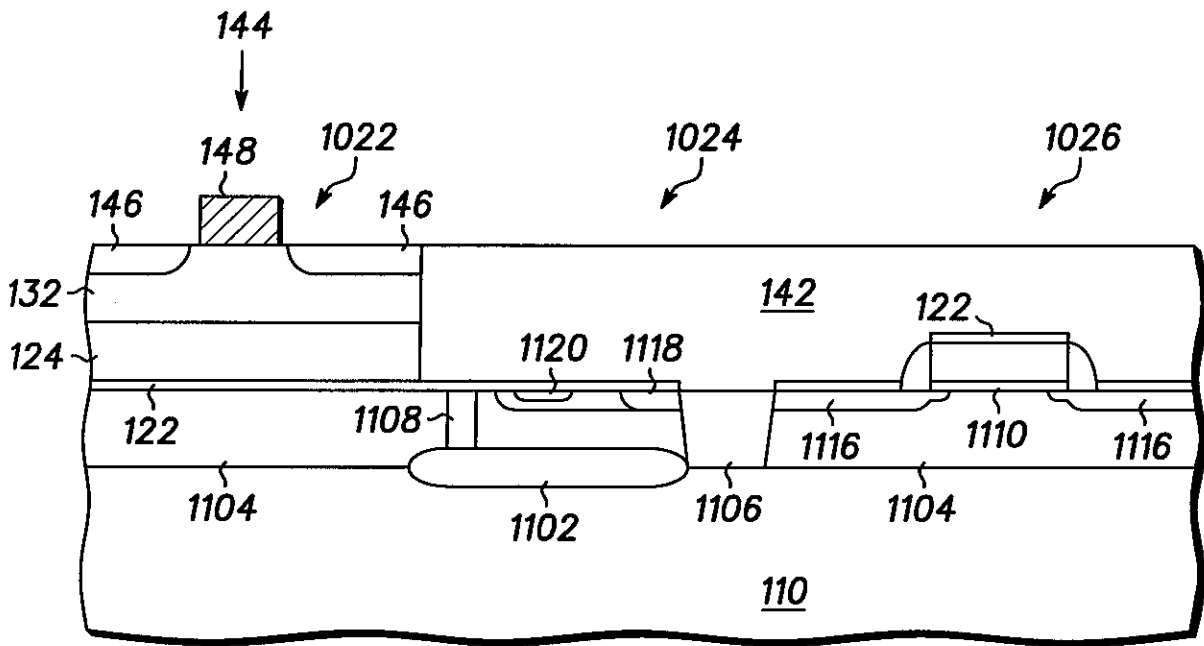


[illegible]

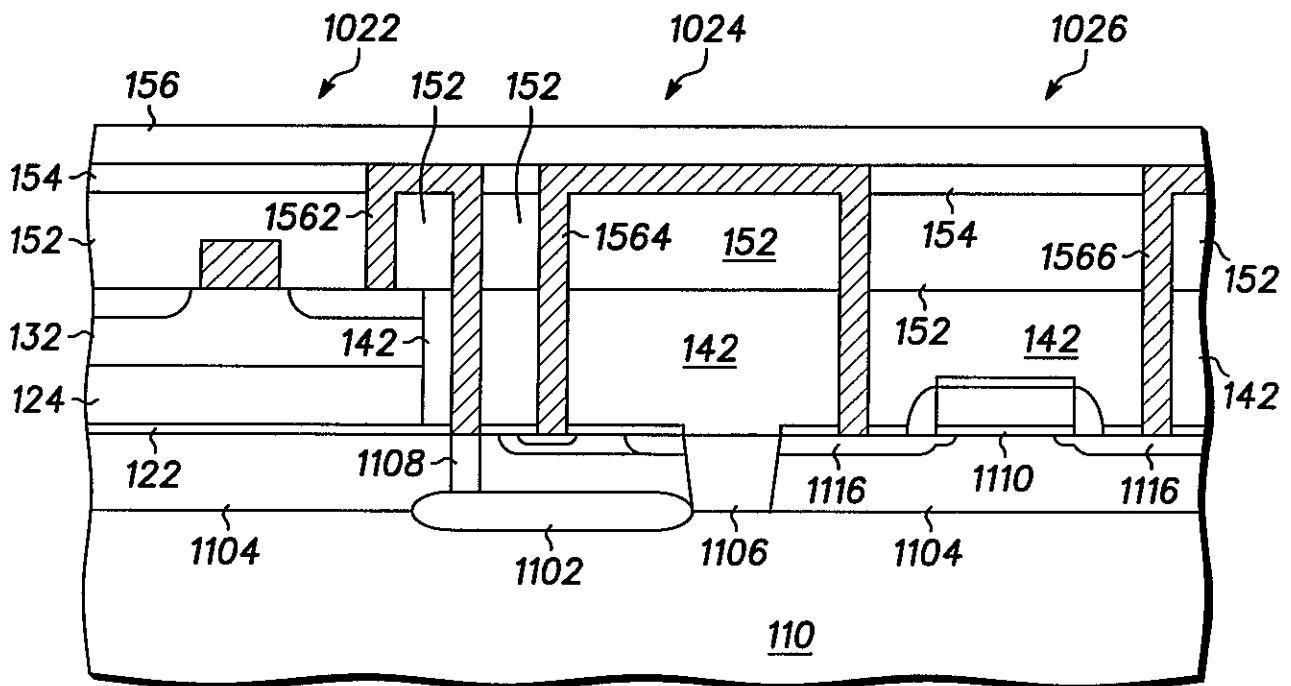
This cross-sectional view shows a semiconductor device 110. A gate stack 1022 is formed on a substrate 1104. The gate stack includes a gate dielectric 1024 and a gate electrode 1026. A contact structure 1102 is formed in the substrate 1104, with a contact plug 1108 and a contact pad 1110. The contact pad 1110 is surrounded by a protective layer 1116. A gate electrode 1118 is positioned over the contact pad 1110, and a gate electrode 1117 is positioned over the contact plug 1108. A gate electrode 122 is positioned over the gate electrode 1118. A gate electrode 124 is positioned over the gate electrode 122. A gate electrode 132 is positioned over the gate electrode 124.

102 *FIG. 9*

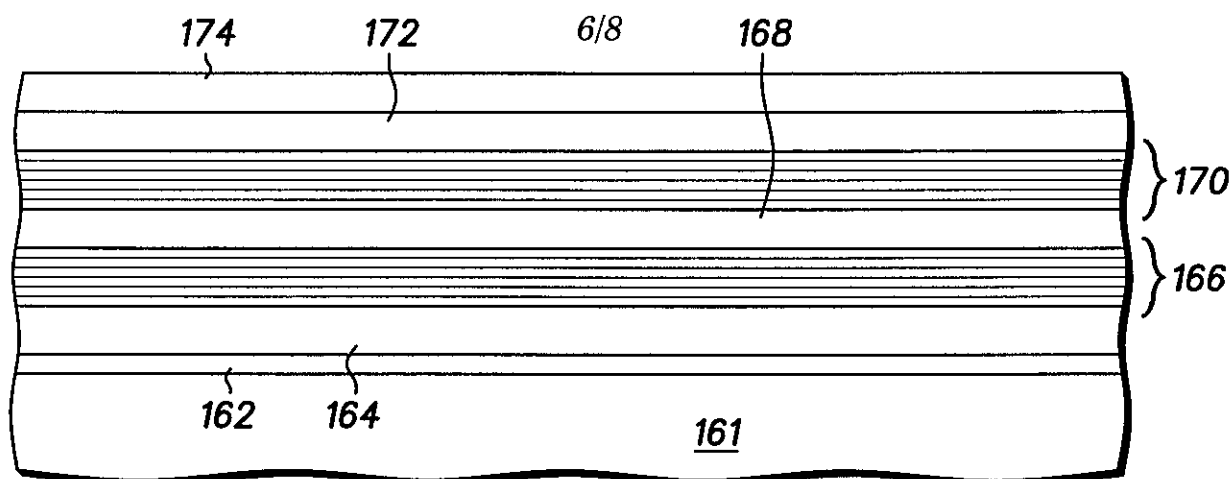
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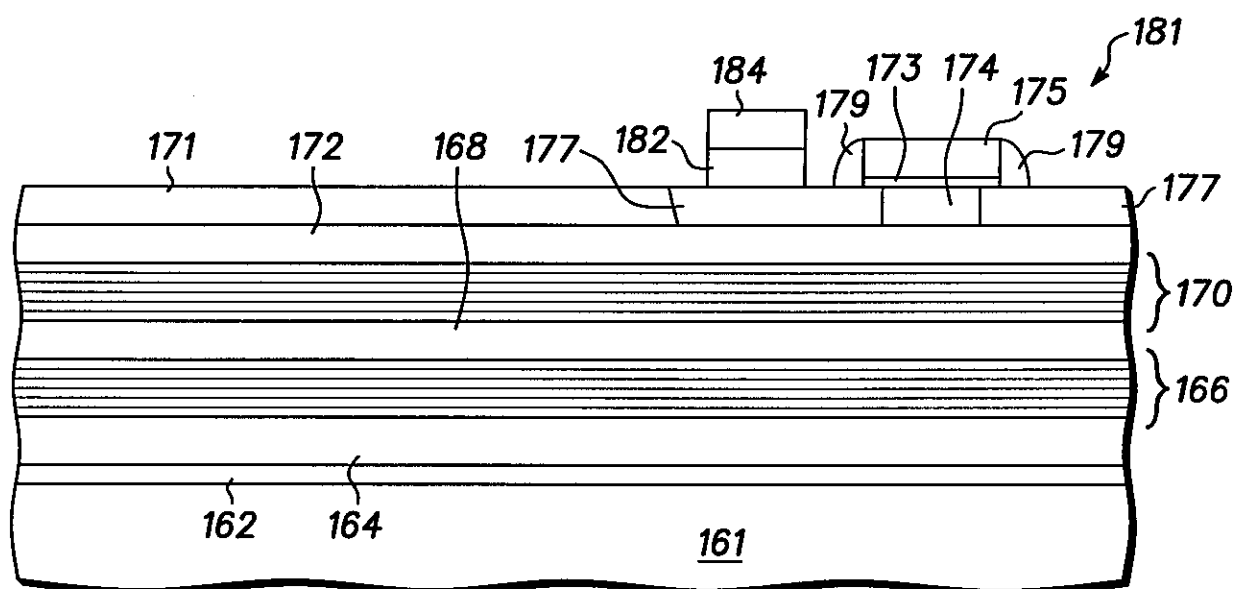
102 **FIG. 10**



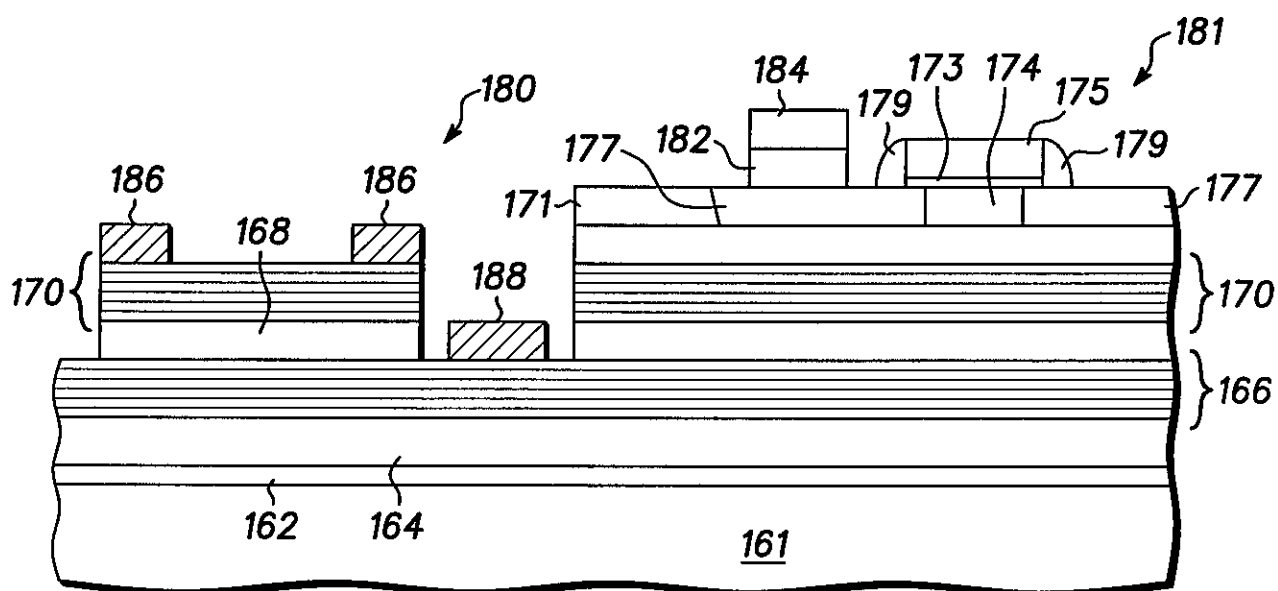
102 **FIG. 11**



160 **FIG. 12**



160 **FIG. 13**



160 **FIG. 14**

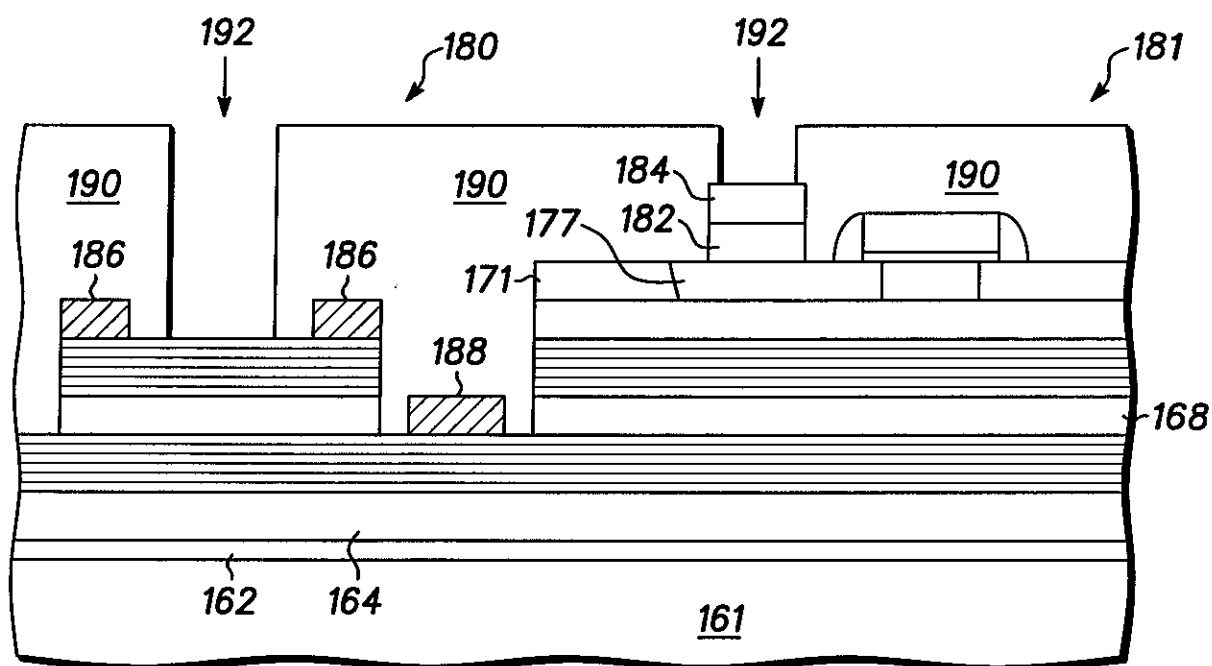


FIG. 15

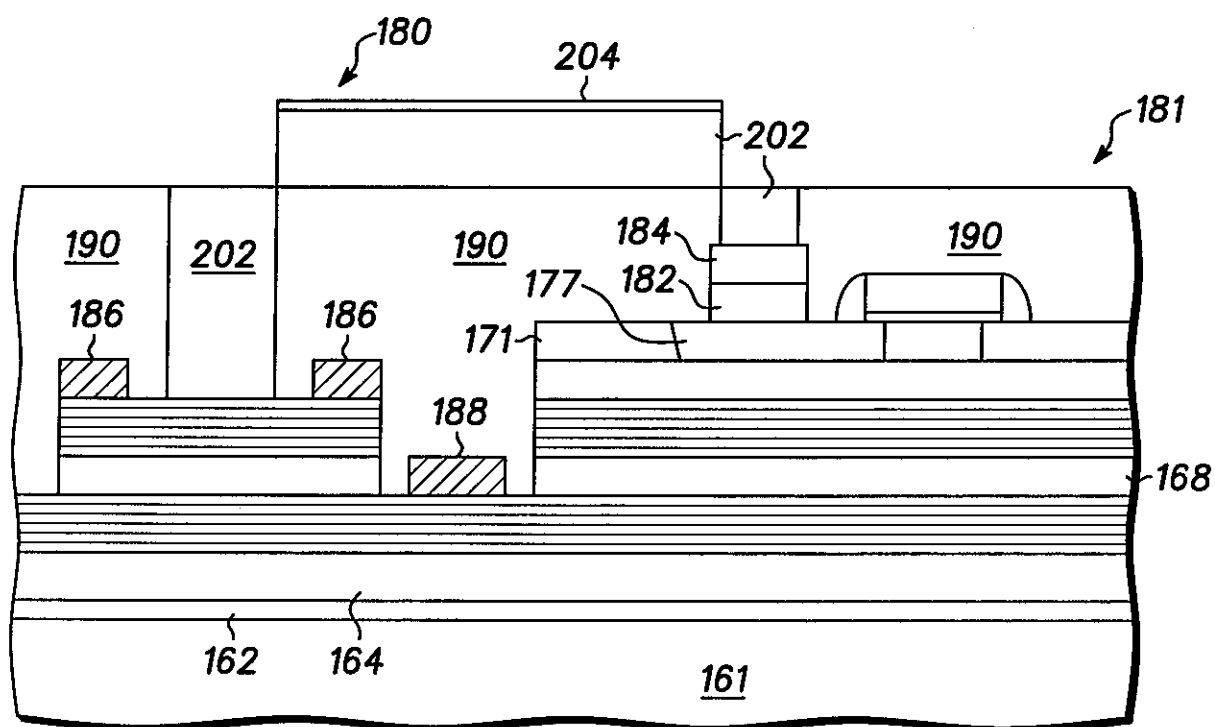


FIG. 16

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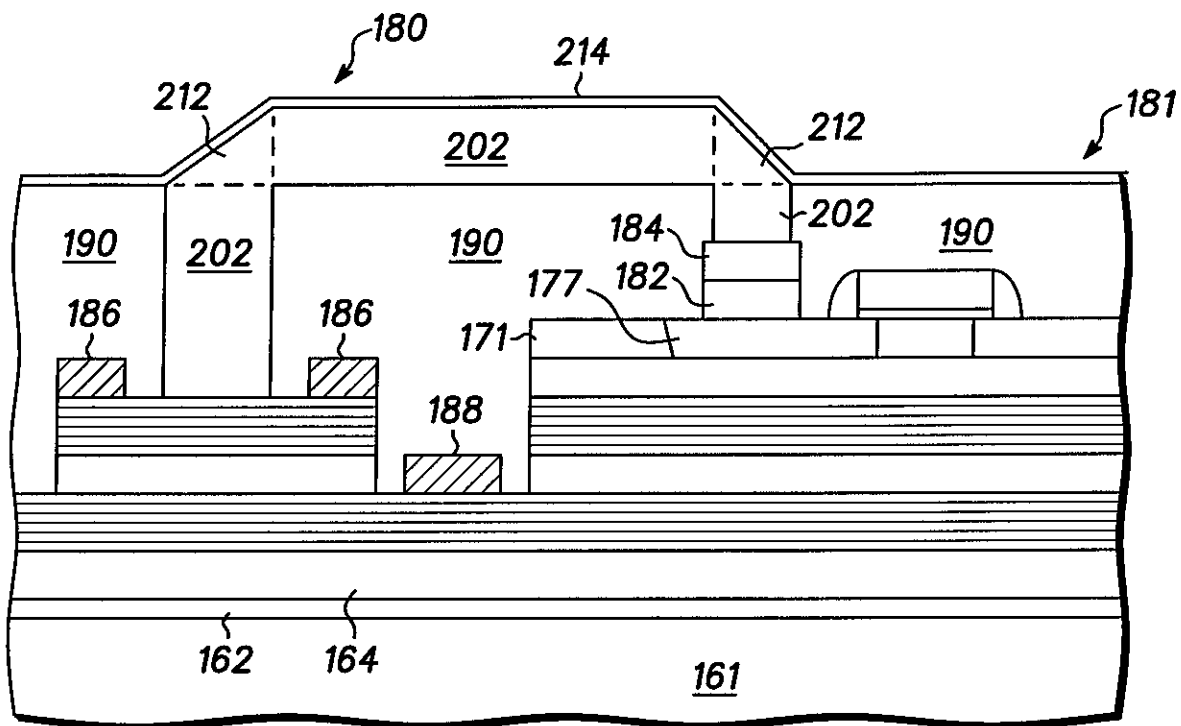


FIG. 17

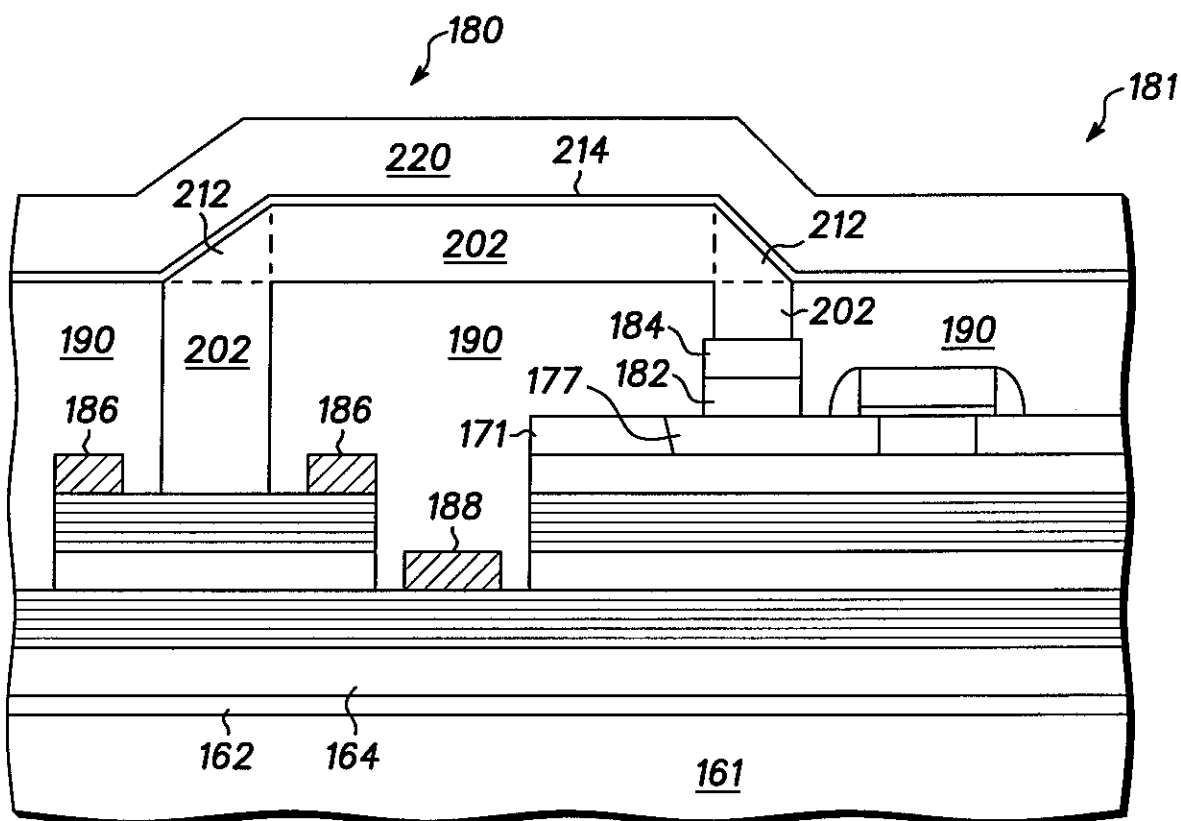


FIG. 18